MMBT3904WG

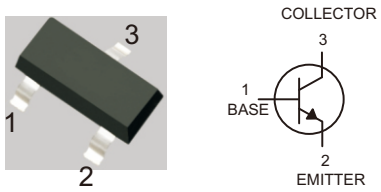
NPN TRANSISTOR

FEATURES

- Complementary to MMBT3906WG
- Epitaxial planar die construction

PINNING

PIN	DESCRIPTION
1	BASE
2	EMITTER
3	COLLECTOR



Simplified outline SOT-323 and symbol

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector–Base Voltage	V_{CBO}	60	V
Collector–Emitter Voltage	V_{CEO}	40	V
Emitter–Base Voltage	V_{EBO}	6	V
Collector Current — Continuous	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10uA, I_E = 0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1 mA, I_B = 0	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10uA, I_C = 0	6			V
Collector cut-off current	I_{CEX}	V_{CE} = 30V, V_{EB} = 3V			50	nA
Collector cut-off current	I_{CBO}	V_{CB} = 60V, I_E = 0			100	nA
Emitter cut-off current	I_{EBO}	V_{EB} = 5V, I_C = 0			100	nA
DC current gain	h_{FE1}	V_{CE} = 1V, I_C = 10mA	100		300	
	h_{FE2}	V_{CE} = 1V, I_C = 50mA	60			
	h_{FE3}	V_{CE} = 1V, I_C = 100mA	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 50mA, I_B = 5mA			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = 50mA, I_B = 5mA			0.95	V
Transition frequency	f_T	V_{CE} = 20V, I_C = 10mA, f=100MHz	300			MHz
Delay time	t_d	V_{CC} = 3V, V_{BE} = -0.5V			35	ns
Rise time	t_r	I_C = 10mA, I_{B1} = 1mA			35	ns
Storage time	t_s	V_{CC} = 3V, I_C = 10mA			200	ns
Fall time	t_f	I_{B1}= I_{B2}= 1mA			50	ns

TYPICAL CHARACTERISTICS

Fig 1. Static characteristics

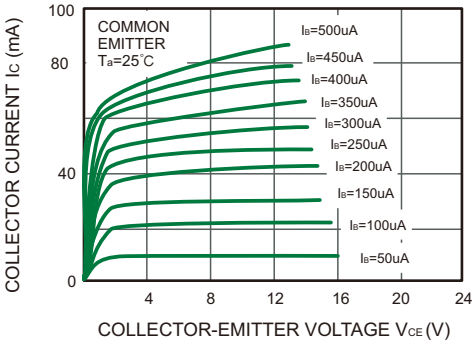


Fig 2. PC —— Ta

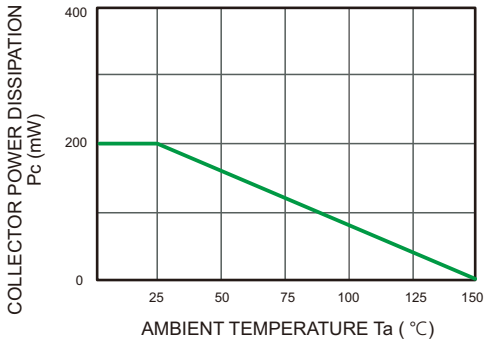


Fig 3. Cob / Cib —— VCB / VEB

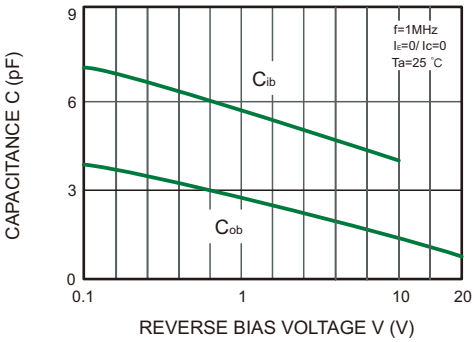


Fig 4. VCEsat —— IC

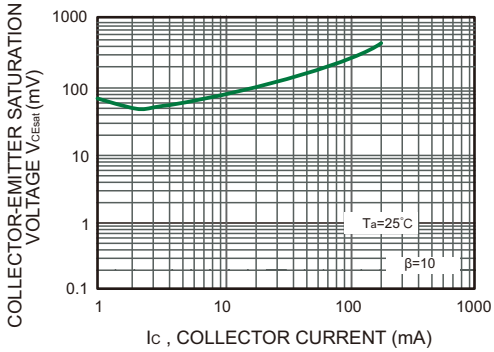


Fig 5. hFE--IC

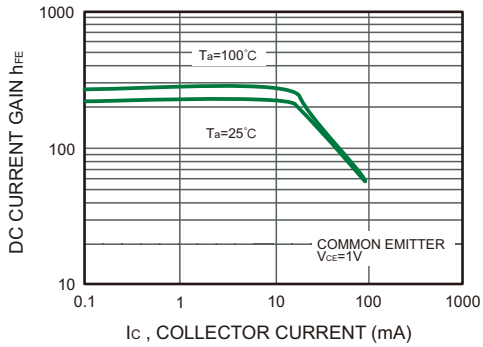


Fig 6. VBEsat —— IC

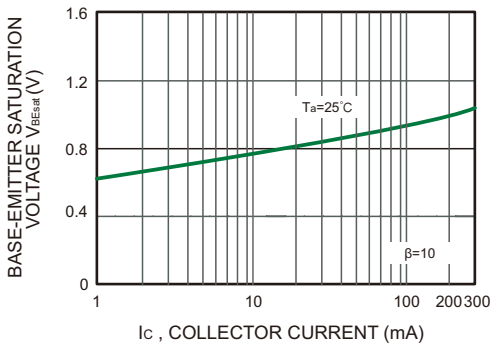


Fig 7. IC —— VBE

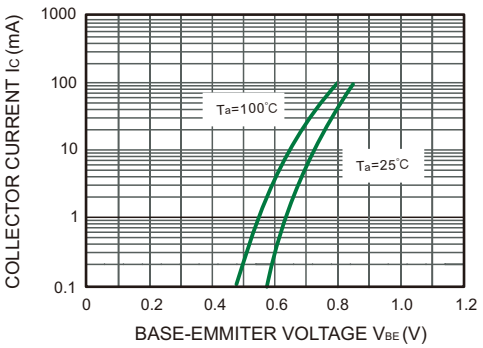
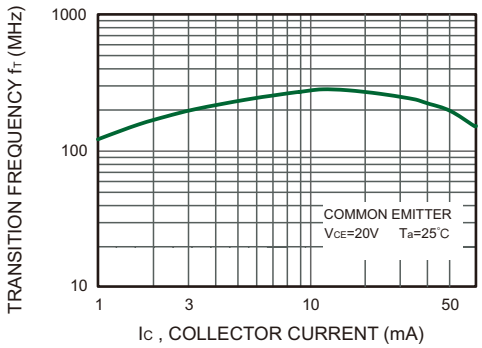
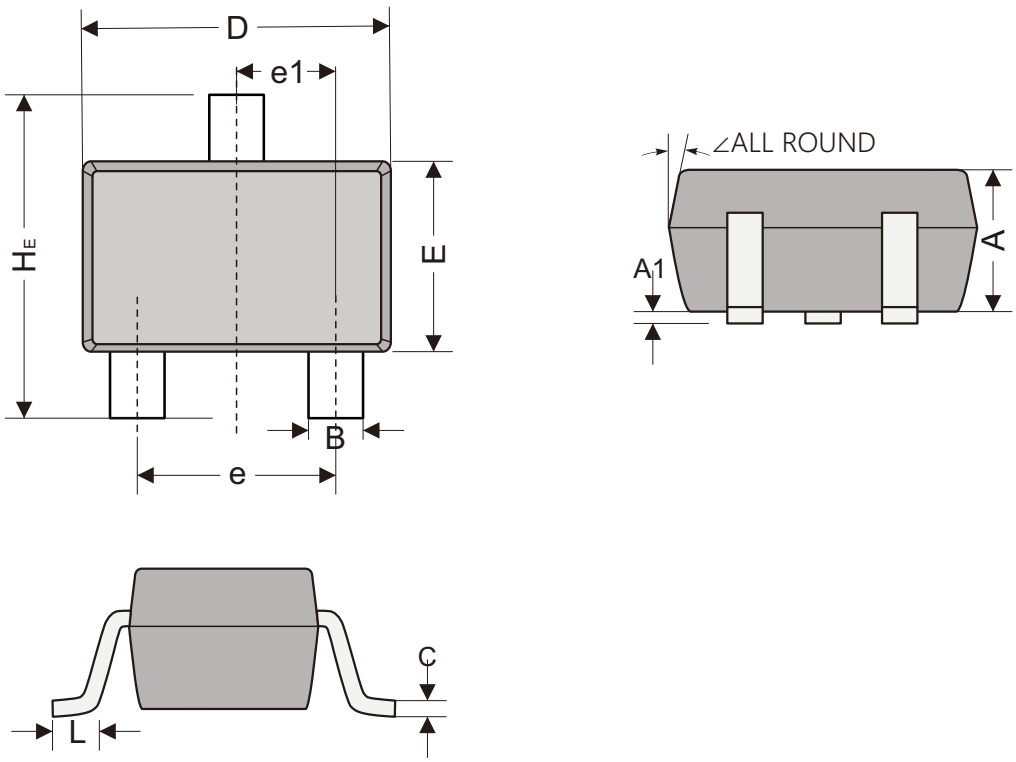


Fig 8. fT ——IC



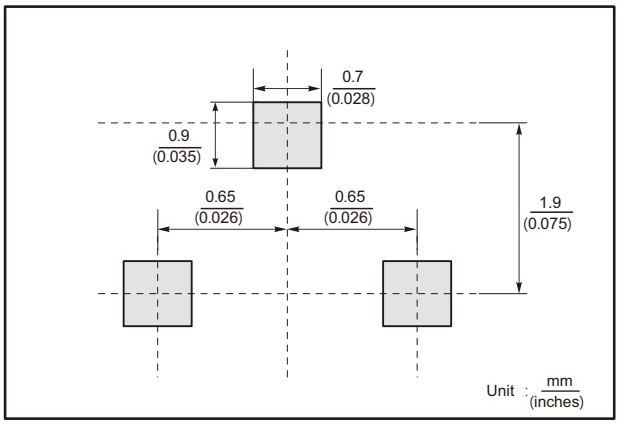
SOT-323 Package Outline Dimensions



SOT-323 mechanical data

UNIT		A	A1	B	C	D	E	e	e1	L	HE
mm	max	1.00	0.10	0.40	0.25	2.20	1.35	1.40	0.65 (BSC)	0.425	2.40
	min	0.80	0.00	0.30	0.10	1.80	1.15	1.20		REF	2.00
mil	max	39.37	3.94	15.75	9.84	86.61	53.15	55.12	25.59 (BSC)	16.73	94.49
	min	31.50	0.00	11.81	3.94	70.87	45.28	47.24		REF	78.74

The recommended mounting pad size



Marking

Type number	Marking code
MMBT3904WG	1AM

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